

- 11 -
CLAIMS

1. A semiconductor device comprising:
 - a semiconductor element;
 - 5 a heat sink; and
 - an intermediate layer provided between the semiconductor element and the heat sink to moderate thermal stress.
2. A semiconductor device according to claim 1, wherein the intermediate layer
10 for moderating thermal stress comprises a carbon-copper composite material.
3. A semiconductor device comprising:
 - a semiconductor element;
 - a heat sink;
 - 15 a laminar plate provided between the semiconductor element and the heat sink so as to include an intermediate layer for moderating thermal stress.
4. A semiconductor device according to claim 3, wherein the laminar plate comprises:
 - 20 a first metal plate bonded to the semiconductor element;
 - the intermediate layer for moderating thermal stress, bonded to the opposite side of the first metal plate from the semiconductor element;
 - a second metal plate bonded to the opposite side of the intermediate layer from the side thereof bonded to the first metal plate;
 - 25 an insulating member bonded to the opposite side of the second metal plate to the side thereof bonded to the intermediate layer; and
 - a third metal plate bonded to the opposite side of the insulating member

to the side thereof bonded to the second metal plate.

5. A semiconductor device according to claim 4, wherein the thickness of the second metal plate and the thickness of the third metal plate are equal.

5

6. A semiconductor device according to claim 3, wherein the intermediate layer for moderating thermal stress comprises a carbon-copper composite material.